FCH040N65S3

MOSFET – Power, N-Channel, SUPERFET® III, Easy Drive

650 V, 65 A, 40 mΩ

Description

SUPERFET III MOSFET is ON Semiconductor's brand−new high voltage super−junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on−resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provides superior switching performance, and withstand extreme dv/dt rate.

Consequently, SUPERFET III MOSFET Easy drive series helps manage EMI issues and allows for easier design implementation.

Features

- 700 V @ T_J = 150°C
- Typ. $R_{DS(on)}$ = 35.4 mΩ
- Ultra Low Gate Charge (Typ. Q_g = 136 nC)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)}$ = 1154 pF)
- 100% Avalanche Tested
- These Devices are Pb−Free and are RoHS Compliant

Applications

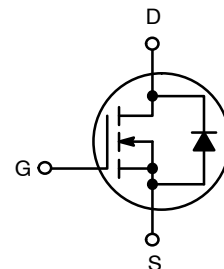- Telecom / Server Power Supplies
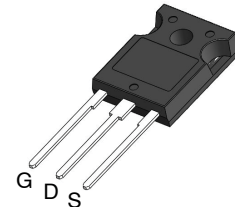- Industrial Power Supplies
- UPS / Solar

ON Semiconductor®

V_{DSS}	$R_{DS(ON)}$ MAX	I_D MAX
650 V	40 mΩ @ 10 V	65 A

POWER MOSFET

TO−247 LONG LEADS
CASE 340CH

MARKING DIAGRAM

$Y&Z&3&K
FCH
040N65S3

$Y	= ON Semiconductor Logo
&Z	= Assembly Plant Code
&3	= Data Code (Year & Week)
&K	= Lot
FCH040N65S3	= Specific Device Code

ORDERING INFORMATION

August, 2019 – Rev. 5

Publication Order Number:
FCH040N65S3/D

FCH040N65S3

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, Unless otherwise noted)

Symbol	Parameter		FCH040N65S3–F155	Unit
V_{DSS}	Drain to Source Voltage		650	V
V_{GSS}	Gate to Source Voltage	– DC	±30	V
		– AC (f > 1 Hz)	±30	
I_D	Drain Current	– Continuous (T_C = 25°C)	65	A
		– Continuous (T_C = 100°C)	41	
I_{DM}	Drain Current	– Pulsed (Note 1)	162.5	A
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		358	mJ
I_{AS}	Avalanche Current (Note 2)		8.1	A
E_{AR}	Repetitive Avalanche Energy (Note 1)		4.17	mJ
dv/dt	MOSFET dv/dt		100	V/ns
	Peak Diode Recovery dv/dt (Note 3)		20	
P_D	Power Dissipation	(T_C = 25°C)	417	W
		– Derate Above 25°C	3.33	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		−55 to +150	°C
T_L	Maximum Lead Temperature for Soldering, 1/8″ from Case for 5 seconds		300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. Repetitive rating: pulse width limited by maximum junction temperature.
2. I_{AS} = 8.1 A, R_G = 25 Ω, starting T_J = 25°C.
3. $I_{SD} \leq$ 32.5 A, di/dt $\leq$ 200 A/µs, $V_{DD} \leq$ 400 V, starting T_J = 25°C.

THERMAL CHARACTERISTICS

Symbol	Parameter	FCH040N65S3–F155	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
FCH040N65S3–F155	FCH040N65S3	TO–247 G03	Tube	N/A	N/A	30 Units

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain to Source Breakdown Voltage	V_{GS} = 0 V, I_D = 1 mA, T_J = 25°C	650	–	–	V
		V_{GS} = 0 V, I_D = 1 mA, T_J = 150°C	700	–	–	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	I_D = 1 mA, Referenced to 25°C	–	0.64	–	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 650 V, V_{GS} = 0 V	–	–	1	µA
		V_{DS} = 520 V, T_C = 125°C	–	4.5	–	
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±30 V, V_{DS} = 0 V	–	–	±100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 1.7 mA	2.5	–	4.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 32.5 A	–	35.4	40	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 20 V, I_D = 32.5 A	–	46	–	S

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted) (continued)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = 400 V, V_{GS} = 0 V, f = 1 MHz	–	4740	–	pF
C_{oss}	Output Capacitance		–	120	–	pF
$C_{oss(eff.)}$	Effective Output Capacitance	V_{DS} = 0 V to 400 V, V_{GS} = 0 V	–	1154	–	pF
$C_{oss(er.)}$	Energy Related Output Capacitance	V_{DS} = 0 V to 400 V, V_{GS} = 0 V	–	171	–	pF
$Q_{g(tot)}$	Total Gate Charge at 10 V	V_{DS} = 400 V, I_D = 32.5 A, V_{GS} = 10 V (Note 4)	–	136	–	nC
Q_{gs}	Gate to Source Gate Charge		–	33	–	nC
Q_{gd}	Gate to Drain "Miller" Charge		–	59	–	nC
ESR	Equivalent Series Resistance	f = 1 MHz	–	0.7	–	Ω
SWITCHING CHARACTERISTICS						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 400 V, I_D = 32.5 A, V_{GS} = 10 V, R_g = 3.3 Ω (Note 4)	–	35	–	ns
t_r	Turn-On Rise Time		–	51	–	ns
$t_{d(off)}$	Turn-Off Delay Time		–	95	–	ns
t_f	Turn-Off Fall Time		–	30	–	ns
SOURCE-DRAIN DIODE CHARACTERISTICS						
I_S	Maximum Continuous Drain to Source Diode Forward Current		–	–	65	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		–	–	162.5	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0 V, I_{SD} = 32.5 A	–	–	1.2	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_{SD} = 32.5 A, dI_F/dt = 100 A/µs	–	534	–	ns
Q_{rr}	Reverse Recovery Charge		–	13.6	–	µC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
4. Essentially independent of operating temperature typical characteristics.

TYPICAL PERFORMANCE CHARACTERISTICS
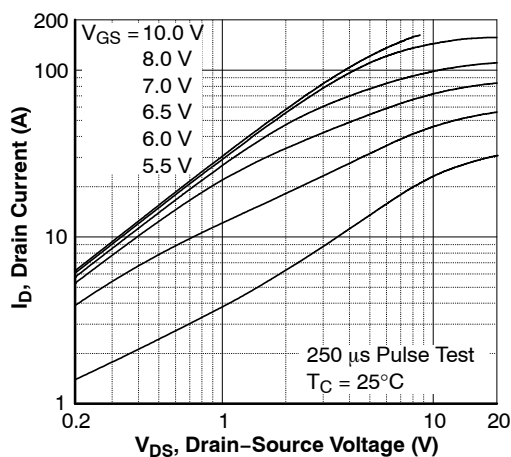
Figure 1. On−Region Characteristics
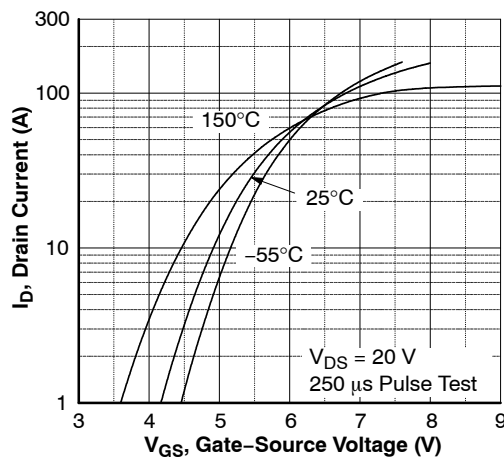
Figure 2. Transfer Characteristics

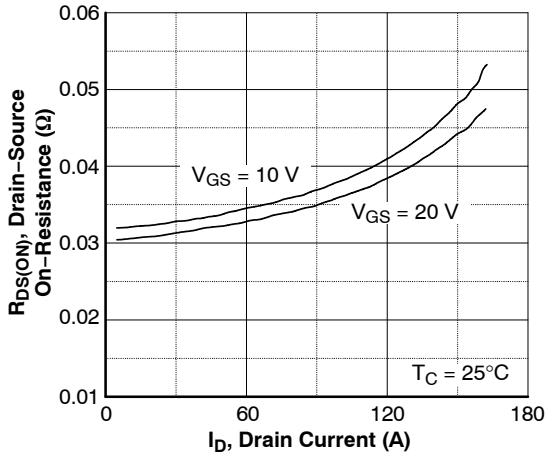**TYPICAL PERFORMANCE CHARACTERISTICS** (continued)

Figure 3. On−Resistance Variation vs.
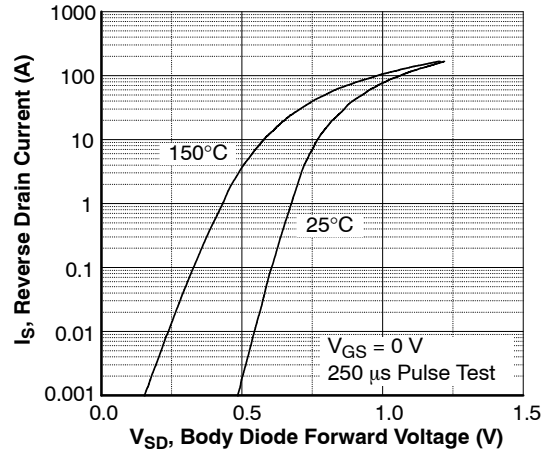Drain Current and Gate Voltage

Figure 4. Body Diode Forward Voltage
Variation vs. Source Current and
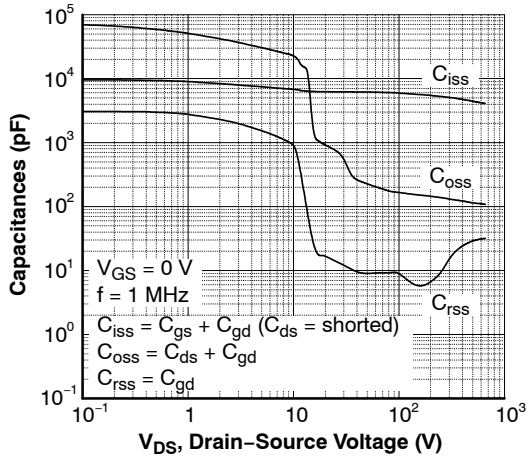Temperature

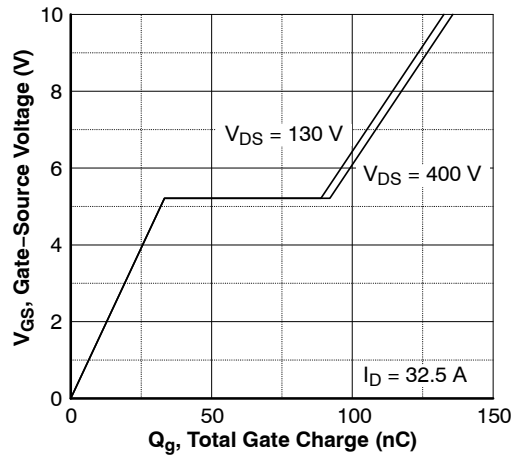Figure 5. Capacitance Characteristics
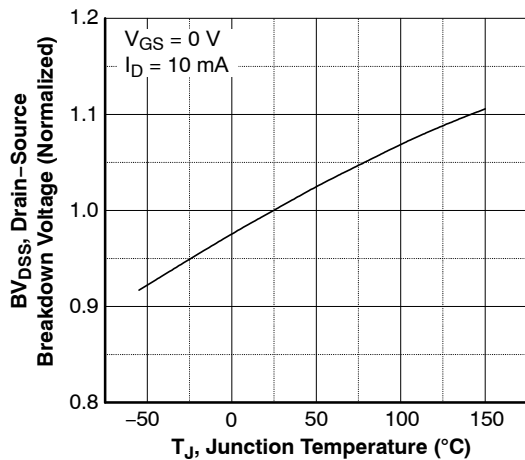

Figure 6. Gate Charge Characteristics

Figure 7. Breakdown Voltage Variation
vs. Temperature

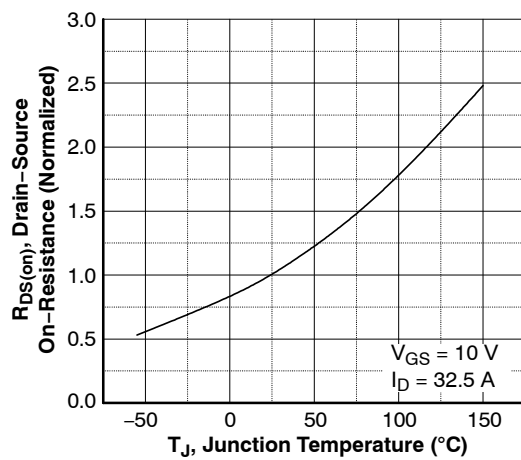Figure 8. On−Resistance Variation
vs. Temperature
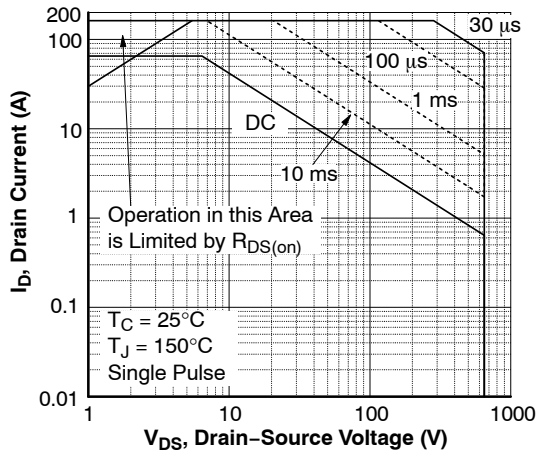
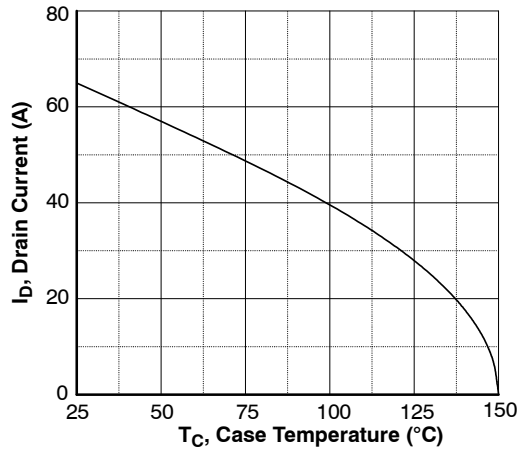## TYPICAL PERFORMANCE CHARACTERISTICS (continued)

Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature
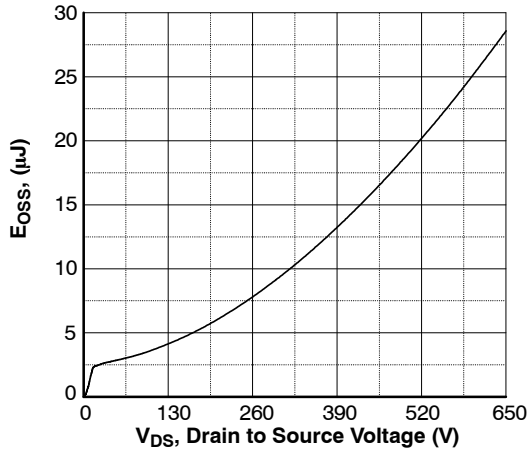
Figure 11. E$_{OSS}$ vs. Drain to Source Voltage
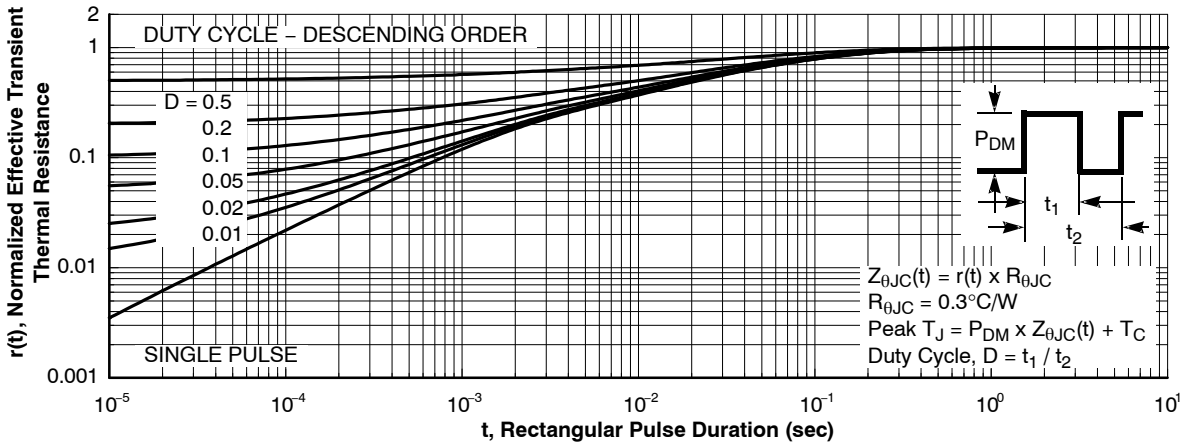
Figure 12. Transient Thermal Response Curve

$Z_{\theta JC}(t) = r(t) \times R_{\theta JC}$
$R_{\theta JC} = 0.3°C/W$
Peak $T_J = P_{DM} \times Z_{\theta JC}(t) + T_C$
Duty Cycle, $D = t_1 / t_2$
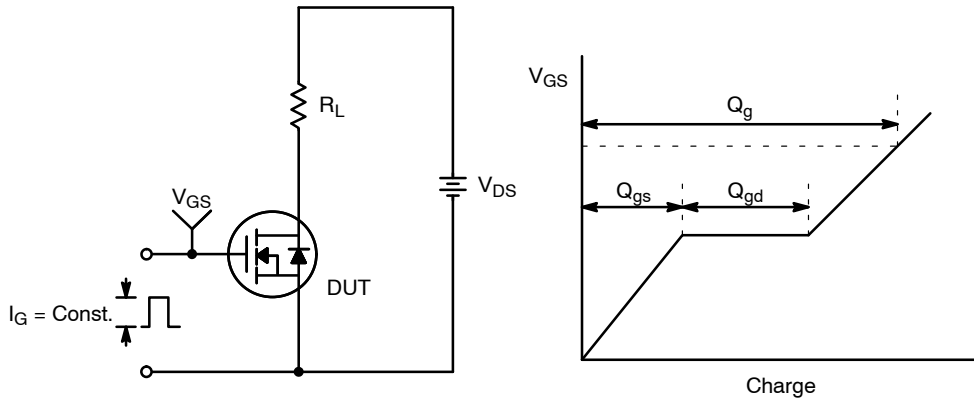
Figure 13. Gate Charge Test Circuit & Waveform
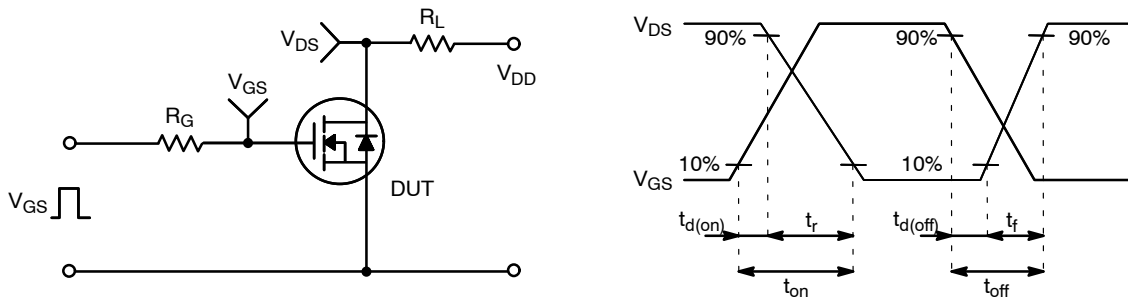
Figure 14. Resistive Switching Test Circuit & Waveforms

$$E_{AS} = \frac{1}{2} \cdot L I_{AS}^{2}$$
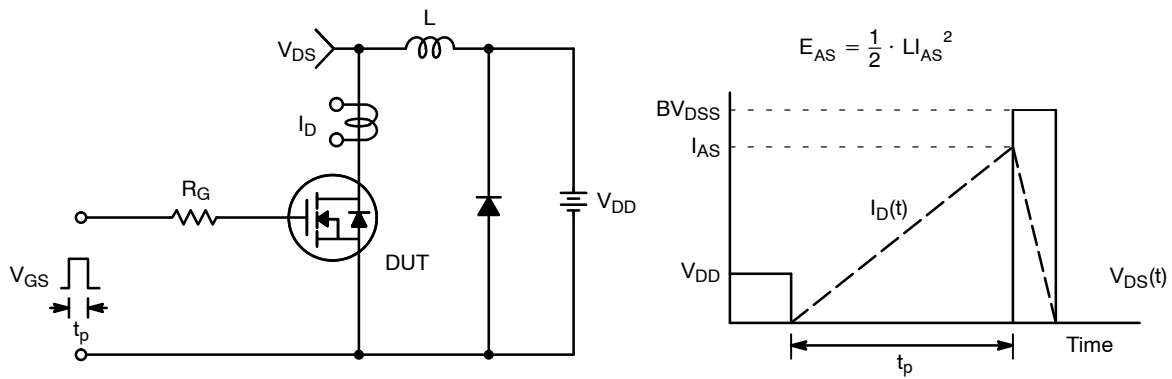
Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms
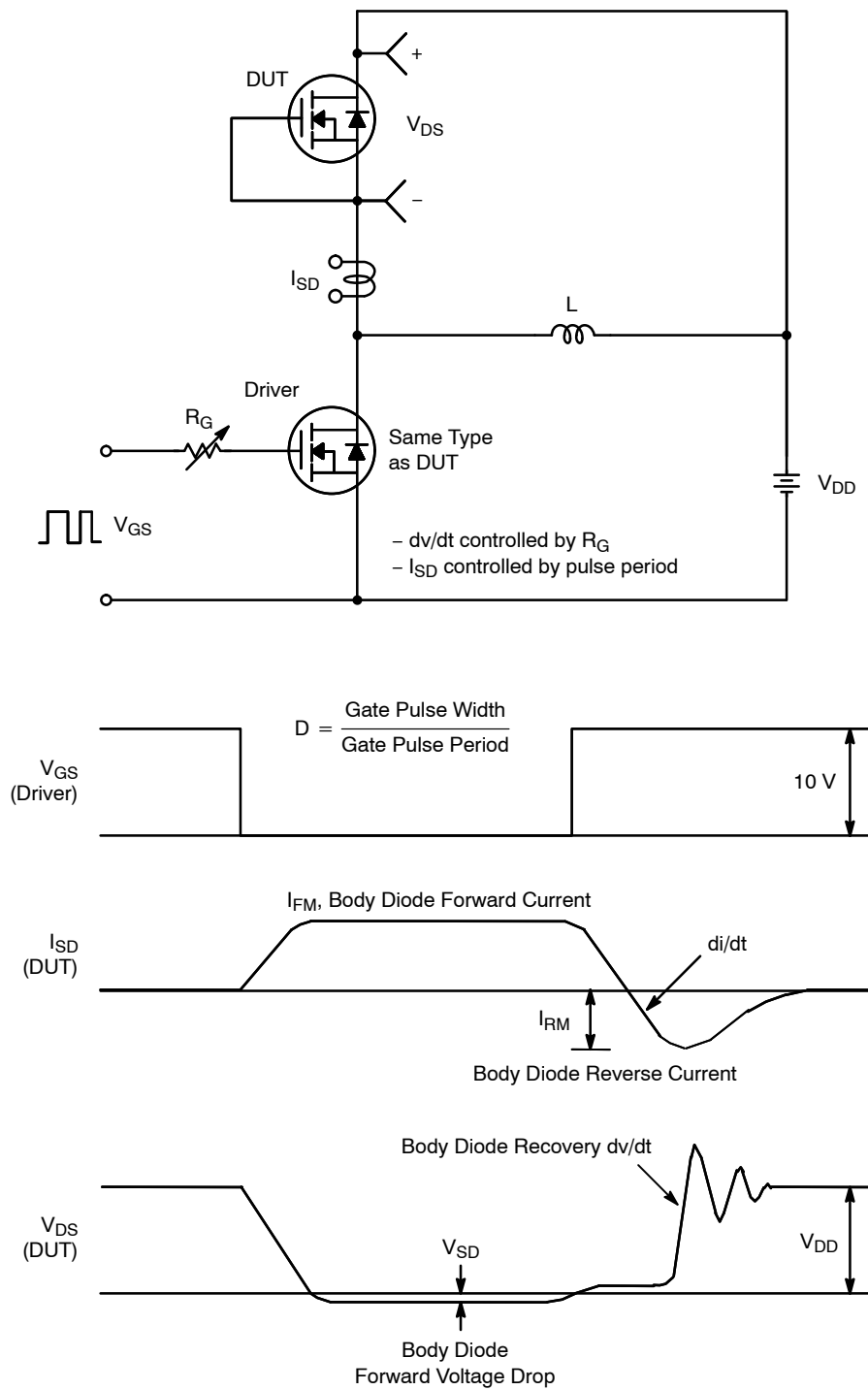
Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

TO−247−3LD
CASE 340CH
ISSUE A

DATE 09 OCT 2019

NOTES: UNLESS OTHERWISE SPECIFIED.

A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD
   FLASH, AND TIE BAR EXTRUSIONS.
B. ALL DIMENSIONS ARE IN MILLIMETERS.
C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

**GENERIC
MARKING DIAGRAM***

XXXXXXXXX
AYWWG

XXXX = Specific Device Code
A   = Assembly Location
Y   = Year
WW   = Work Week
G   = Pb−Free Package

*This information is generic. Please refer to
 device data sheet for actual part marking.
 Pb−Free indicator, "G" or microdot "▪", may
 or may not be present. Some products may
 not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.29	2.475	2.66
A2	1.40	1.50	1.60
D	20.32	20.57	20.82
E	15.37	15.62	15.87
E2	4.96	5.08	5.20
e	~	5.56	~
L	19.75	20.00	20.25
L1	3.69	3.81	3.93
⌀P	3.51	3.58	3.65
Q	5.34	5.46	5.58
S	5.34	5.46	5.58
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D1	13.08	~	~
D2	0.51	0.93	1.35
E1	12.81	~	~
⌀P1	6.61	6.73	6.85

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